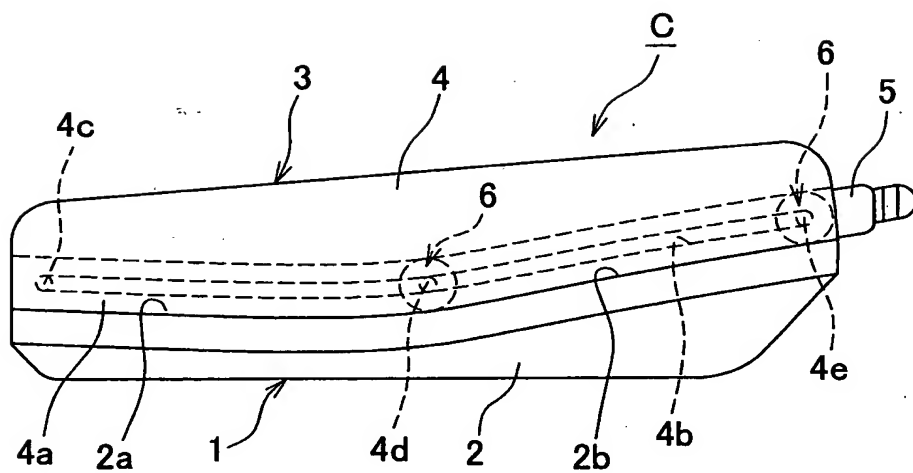


Fig. 1



Fi3

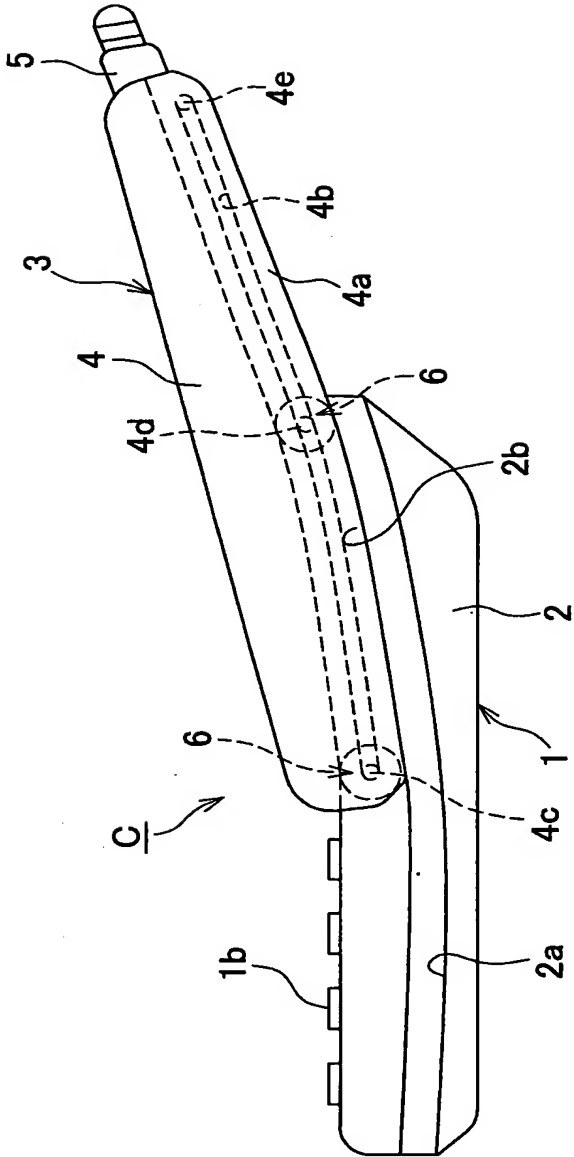


Fig. 4

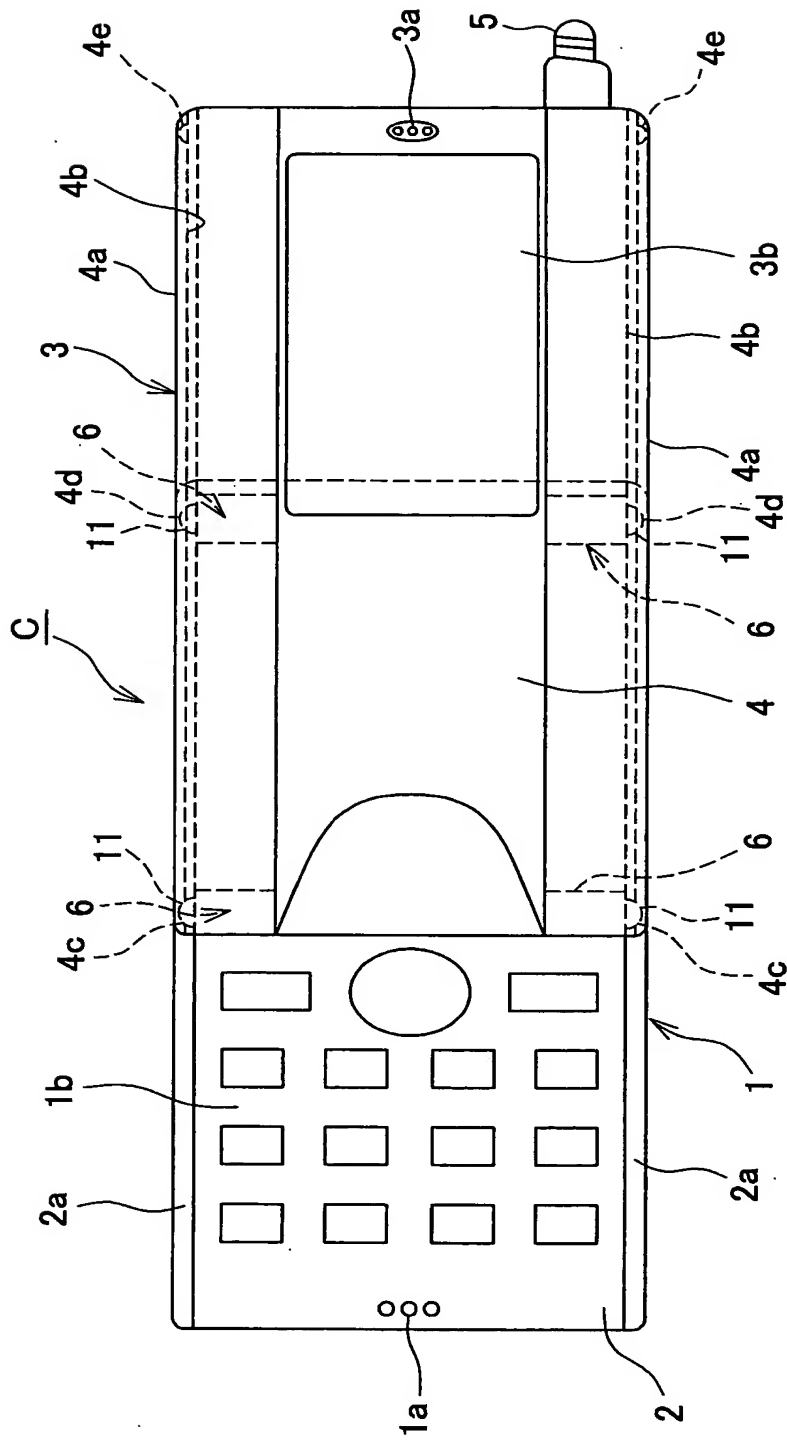


Fig 5

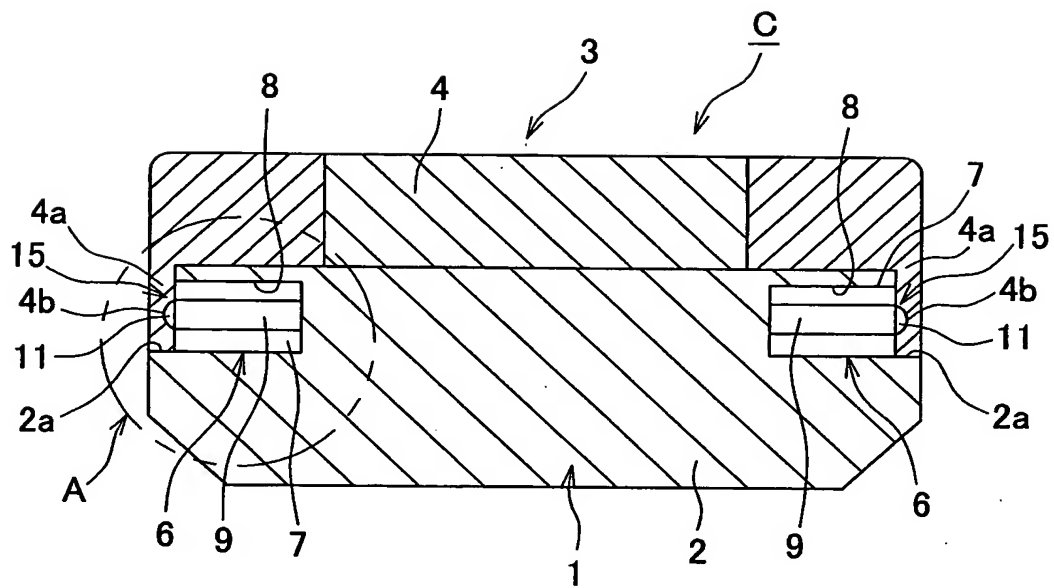


Fig. 6

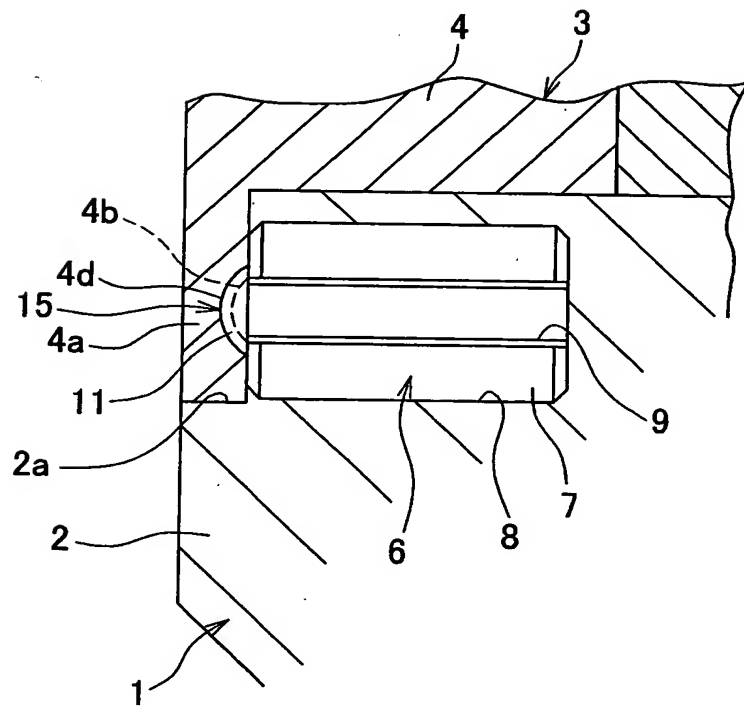


Fig. 8

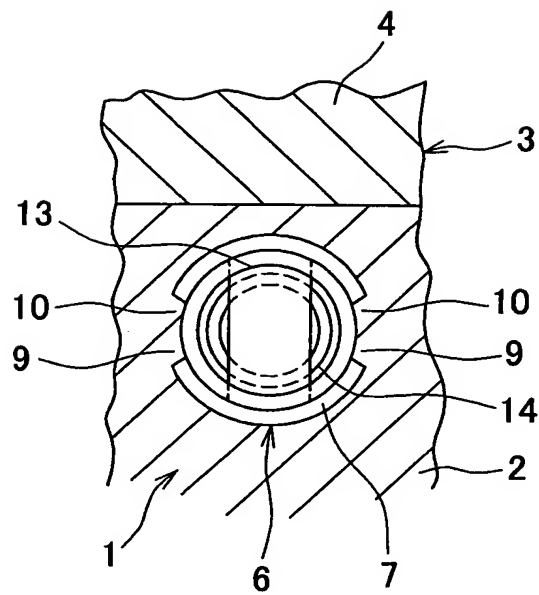


Fig. 9

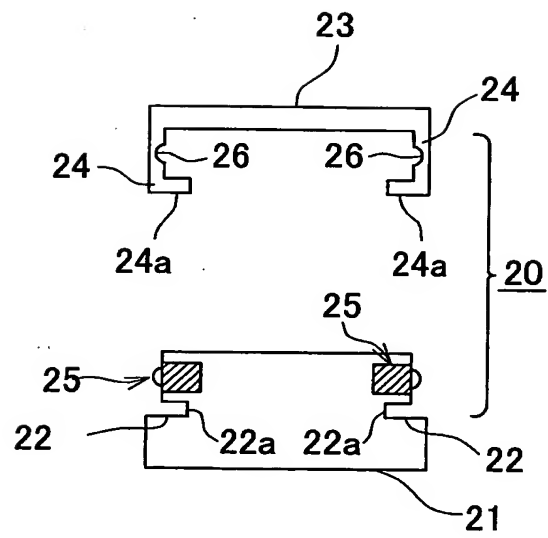


Fig. 1 is a schematic cross-sectional view of a semiconductor device. The device consists of a substrate 31. On the top surface of the substrate 31, there is a central layer 32. Two rectangular regions 35 are formed on the top surface of the layer 32. Each region 35 contains a circular feature 34. Above the regions 35, there is a larger rectangular block 33. The block 33 has two protruding parts 34a on its top surface. A bracket on the right side of the diagram groups the entire assembly as 30.